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INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Mitsutoshi MIYASAKAFILING DATE
March 19, 2002

GROUP

JCS71 U.S. PTO
10/099963

03/19/02

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
LP ↓	5,858,819	01/1999	Miyasaka		
	5,827,773	05/1997	Voutsas		
	6,066,516	5/2000	Miyasaka		
	6,017,719	1/2000	Yiyasaka		
	5,904,770	5/1999	Ohtani et al.		
	6,074,901	6/2000	Ohtani et al.		
	6,121,660	9/2000	Yamazaki et al.		
	6,113,689	9/2000	Moon		

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
LP ↓ ✓	JP-A-4-298020	10/1992	Japan		
	JP-A-4-100210	4/1992	Japan		
	JP-A-8-107067	4/1996	Japan		
	5-129332	5/1993	Japan		
	3-292719	12/1991	Japan		
	3-178124	8/1991	Japan		
	3-72617	3/1991	Japan		
	62-104021	5/1987	Japan		
	6-216044	8/1994	Japan		
	63-151014	6/1988	Japan		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

LP	Levinson, J., et al., "Conductivity Behavior in Polycrystalline Semiconductor Thin Film Transistors," J. Appl. Phys. 53 (2), February 1982, pp. 1193-1202.
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EXAMINER

LON G ATOM

DATE CONSIDERED

7/9/03

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: March 19, 2002